CLAIMS:

1. A method of making a comparatively small substrate compatible for being processed in equipment designed for a larger standard substrate, wherein the standard substrate has a surface in which a cavity is formed, in which cavity the small substrate to be processed is attached by means of a layer of a bonding material, characterized in that the cavity in the standard substrate is formed so as to have a flat bottom, which extends parallel to the surface, and a depth such that, after the small substrate is attached with its rear side to the bottom of the cavity in the surface of the standard substrate by means of said layer of bonding material, the front side of said small substrate forms the free surface which substantially coincides with the surface of the standard substrate.

2. A method as claimed in claim 1, characterized in that the standard substrate is formed by, in succession, providing a layer of silicon oxide on the front side of a standard silicon wafer, attaching the wafer with its front side covered with the silicon oxide layer onto an auxiliary substrate, subjecting the rear side of the silicon wafer to a polishing treatment in order to obtain a thickness of the wafer that corresponds to the depth of the cavity to be formed, and forming the cavity, from the polished rear side, by means of an etch treatment which stops automatically at the layer of silicon oxide.

3. A method as claimed in claim 1, characterized in that the standard substrate is formed by, in succession, subjecting a standard silicon wafer to a polishing treatment from the rear side of the wafer to bring it to a thickness that corresponds to the depth of the cavity to be formed, applying a layer of silicon oxide to the polished rear side, attaching the wafer with its polished rear side covered with the layer of silicon oxide onto an auxiliary substrate, and subsequently forming the cavity from the front side of the wafer by means of an etch treatment that stops automatically at the layer of silicon oxide.

4. A method as claimed in claim 2 or 3, characterized in that the small substrate is attached in the cavity by detachably attaching the small substrate with its flat front side onto a flat auxiliary plate, and, after the small substrate is provided at its rear side with a layer

of bonding material, by pressing the auxiliary plate with the small substrate into the cavity in the surface of the standard substrate, and by removing the auxiliary plate after the adhesive has cured.

5. A method as claimed in claim 4, characterized in that the small substrate is detachably attached onto the auxiliary plate by causing the small substrate to be sucked against the auxiliary plate.

6. A method as claimed in claim 2, 3, 4 or 5, characterized in that the silicon wafer is glued with its front side covered with the silicon oxide layer onto a glass plate that serves as an auxiliary substrate.

7. A method as claimed in claim 6, characterized in that an UV-curable glue is used as the bonding material.

8. A method as claimed in any one of claims 2 through 7, characterized in that the silicon wafer is provided at its polished rear side with aligning characteristics for automatically aligning the standard substrate in photolithographic equipment.

9. A method as claimed in any one of claims 2 through 8, characterized in that the silicon wafer is provided at its polished rear side with an etch mask formed in a silicon nitride layer deposited on the polished side.